

6 to 18 GHz AA618L2-00 GaAs MMIC Amplifier

T-74-13-a

Features

- Feedback Design
- Excellent Broadband
- Performance
- Includes I/O DC Blocks
- Low DC Power Consumption
- E-Beam Written Gate for Uniformity with High Performance
- On Wafer Probe Pads
- Size: 92 x 92 x 6

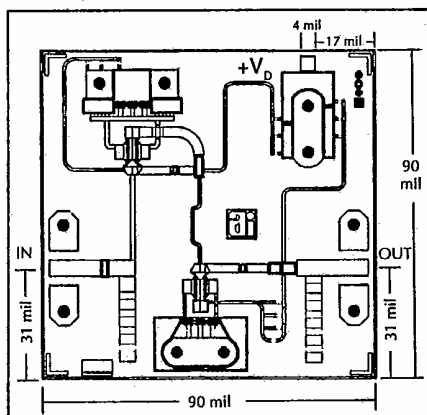
Description

The AA618L2-00 features two 0.5 x 300 micron ion-implanted MESFET devices with E-beam written gates for excellent uniformity and reproducibility. Series and shunt feedback design techniques give improved gain flatness and input/output VSWR. These features result in an easily cascadable chip. Single and dual bias options are available to satisfy a variety of applications.

Electrical Specifications

Frequency	6 to 18 GHz
Small Signal Gain	8 dB, Typ.
Flatness	± 0.75 , Typ. ± 1.0 , Max.
Input/Output VSWR	2:1, Typ. 2.2:1, Max.
Noise Figure	7.5 dB, Max.
P_{1dB}	10 dBm, Typ.
I_{ds} , at $V_{ds}=3V$ and $V_{gs}=-1V$	80 mA Typ., 100 mA Max.

Chip Configuration



Typical Performance

